

# Advanced Power MOSFET

# IRLR/U034A

## FEATURES

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10  $\mu$ A (Max.) @  $V_{DS} = 60V$
- Lower  $R_{DS(ON)}$  : 0.033  $\Omega$  (Typ.)

$$BV_{DSS} = 60 V$$

$$R_{DS(on)} = 0.046 \Omega$$

$$I_D = 23 A$$

D-PAK I-PAK



1. Gate 2. Drain 3. Source

## Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	60	V
$I_D$	Continuous Drain Current ( $T_C=25^\circ C$ )	23	A
	Continuous Drain Current ( $T_C=100^\circ C$ )	14.5	
$I_{DM}$	Drain Current-Pulsed ①	80	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulsed Avalanche Energy ②	453	mJ
$I_{AR}$	Avalanche Current ①	23	A
$E_{AR}$	Repetitive Avalanche Energy ①	4.2	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
$P_D$	Total Power Dissipation ( $T_A=25^\circ C$ ) *	2.5	W
	Total Power Dissipation ( $T_C=25^\circ C$ )	42	W
	Linear Derating Factor	0.33	W/ $^\circ C$
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	- 55 to +150	$^\circ C$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

## Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	2.94	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient *	--	50	
$R_{\theta JA}$	Junction-to-Ambient	--	110	

\* When mounted on the minimum pad size recommended (PCB Mount).



Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$BV_{DSS}$	Drain-Source Breakdown Voltage	60	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.062	--	V/ $^\circ\text{C}$	$I_D=250\mu A$ See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	1.0	--	2.0	V	$V_{DS}=5V, I_D=250\mu A$
$I_{GSS}$	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=20V$
	Gate-Source Leakage, Reverse	--	--	-100		$V_{GS}=-20V$
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	10	$\mu A$	$V_{DS}=60V$
		--	--	100		$V_{DS}=48V, T_C=125^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.046	$\Omega$	$V_{GS}=5V, I_D=11.5A$ ④
$g_{fs}$	Forward Transconductance	--	18.6	--	$\text{S}$	$V_{DS}=30V, I_D=11.5A$ ④
$C_{iss}$	Input Capacitance	--	970	1260	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ See Fig 5
$C_{oss}$	Output Capacitance	--	334	385		
$C_{rss}$	Reverse Transfer Capacitance	--	131	150		
$t_{d(on)}$	Turn-On Delay Time	--	13	35	ns	$V_{DD}=30V, I_D=30A,$ $R_G=6\Omega$ See Fig 13 ④ ⑤
$t_r$	Rise Time	--	21	55		
$t_{d(off)}$	Turn-Off Delay Time	--	36	80		
$t_f$	Fall Time	--	28	65		
$Q_g$	Total Gate Charge	--	27	35	nC	$V_{DS}=48V, V_{GS}=5V,$ $I_D=30A$ See Fig 6 & Fig 12 ④ ⑤
$Q_{gs}$	Gate-Source Charge	--	9	--		
$Q_{gd}$	Gate-Drain( "Miller" ) Charge	--	12	--		

## Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$I_S$	Continuous Source Current	--	--	23	A	Integral reverse pn-diode in the MOSFET
$I_{SM}$	Pulsed-Source Current ①	--	--	80		
$V_{SD}$	Diode Forward Voltage ④	--	--	1.6	V	$T_J=25^\circ\text{C}, I_S=23A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	--	64	--	ns	$T_J=25^\circ\text{C}, I_F=30A$
$Q_{rr}$	Reverse Recovery Charge	--	0.122	--	$\mu\text{C}$	$di_F/dt=100A/\mu\text{s}$ ④

## Notes :

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature  
 ②  $L=1\text{mH}, I_{AS}=23A, V_{DD}=25V, R_G=27\Omega$ , Starting  $T_J=25^\circ\text{C}$   
 ③  $I_{SD} \leq 30A, di/dt \leq 300A/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^\circ\text{C}$   
 ④ Pulse Test : Pulse Width = 250  $\mu\text{s}$ , Duty Cycle  $\leq 2\%$   
 ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

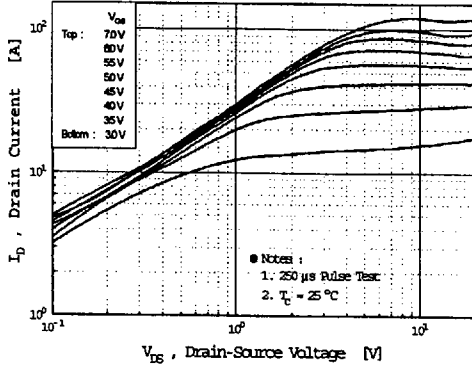


Fig 2. Transfer Characteristics

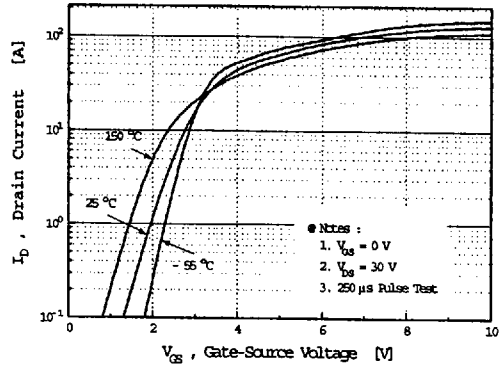


Fig 3. On-Resistance vs. Drain Current

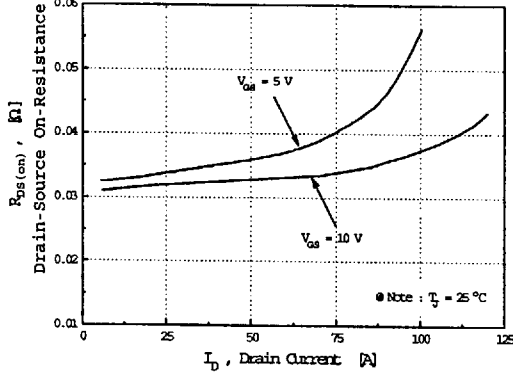


Fig 4. Source-Drain Diode Forward Voltage

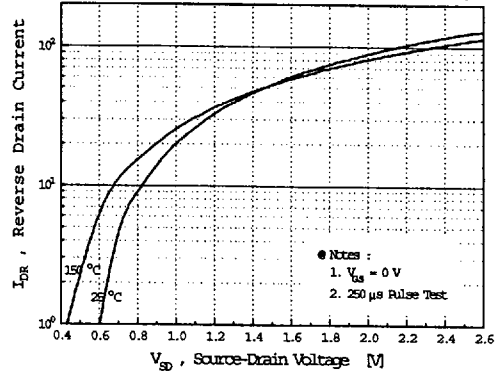


Fig 5. Capacitance vs. Drain-Source Voltage

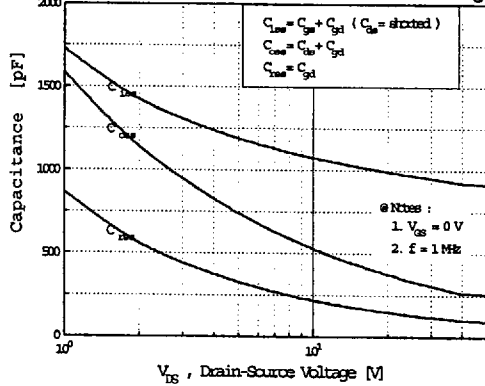
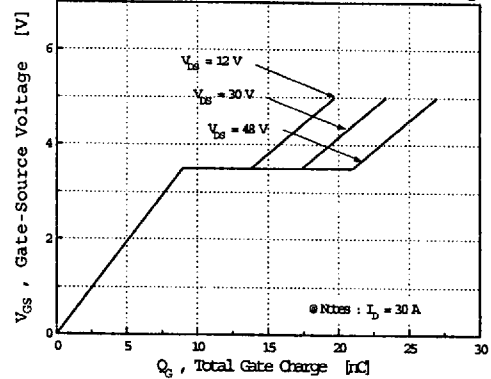
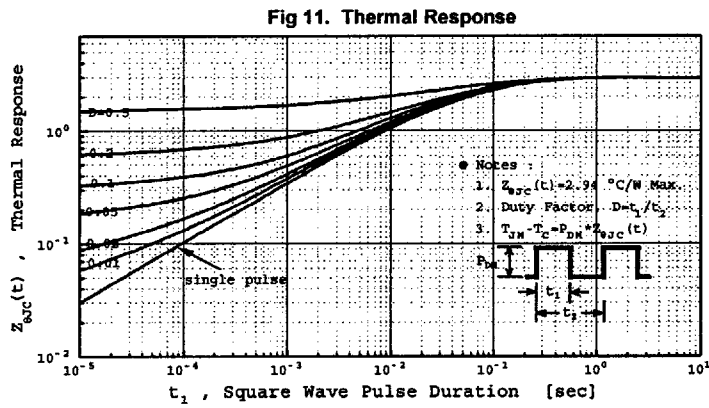
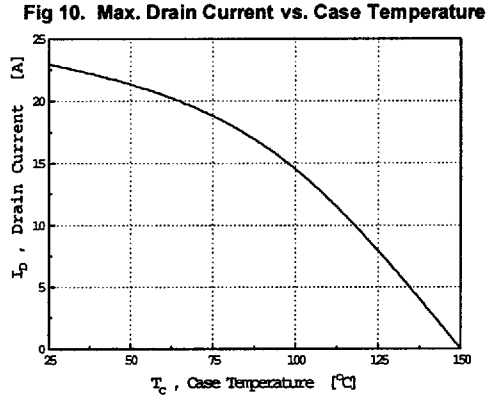
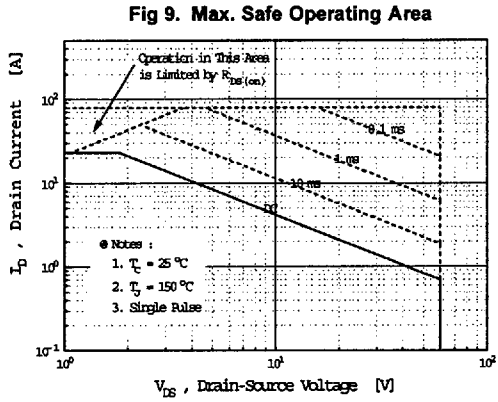
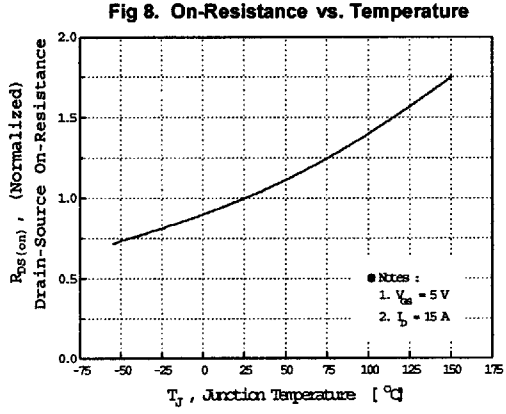
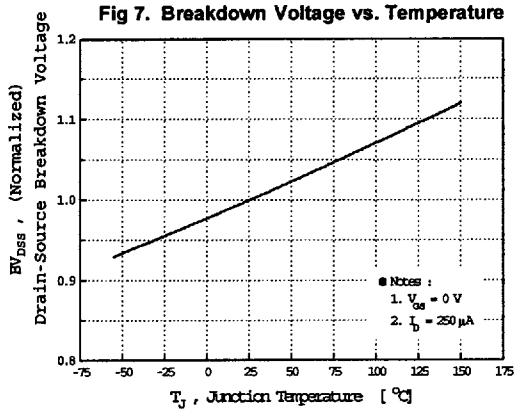
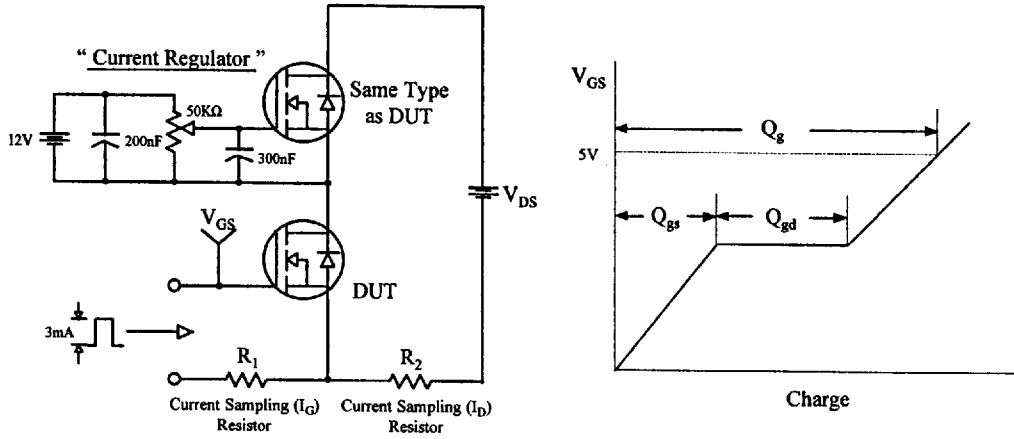


Fig 6. Gate Charge vs. Gate-Source Voltage

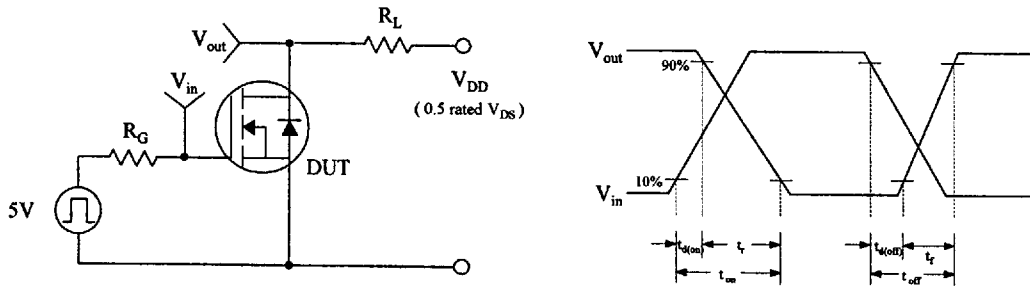




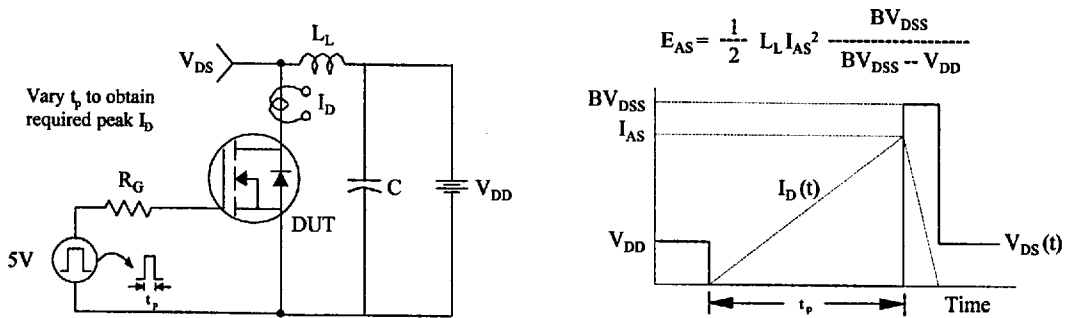
**Fig 12. Gate Charge Test Circuit & Waveform**



**Fig 13. Resistive Switching Test Circuit & Waveforms**



**Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms**



$$E_{AS} = \frac{1}{2} L_L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

